

### DESCRIPTION

The MP18021 is a high frequency, 100V half bridge N-channel power MOSFET driver. Its low side and high side driver channels are independently controlled and matched with less than 5ns in time delay. Under voltage lock-out on both high side and low side supplies force their outputs low in case of insufficient supply. The integrated bootstrap diode reduces external component count.

### FEATURES

- Drives N-channel MOSFET half bridge
- 100V  $V_{BST}$  voltage range
- On-chip bootstrap diode
- Typical 16ns propagation delay time
- Less than 5ns gate drive matching
- Drive 1nF load with 12ns/9ns rise/fall times with 12V VDD
- TTL compatible input
- Less than 150 $\mu$ A quiescent current
- UVLO for both high side and low side
- In SOIC8 EPAD and 3 $\times$ 3mm QFN8 Packages

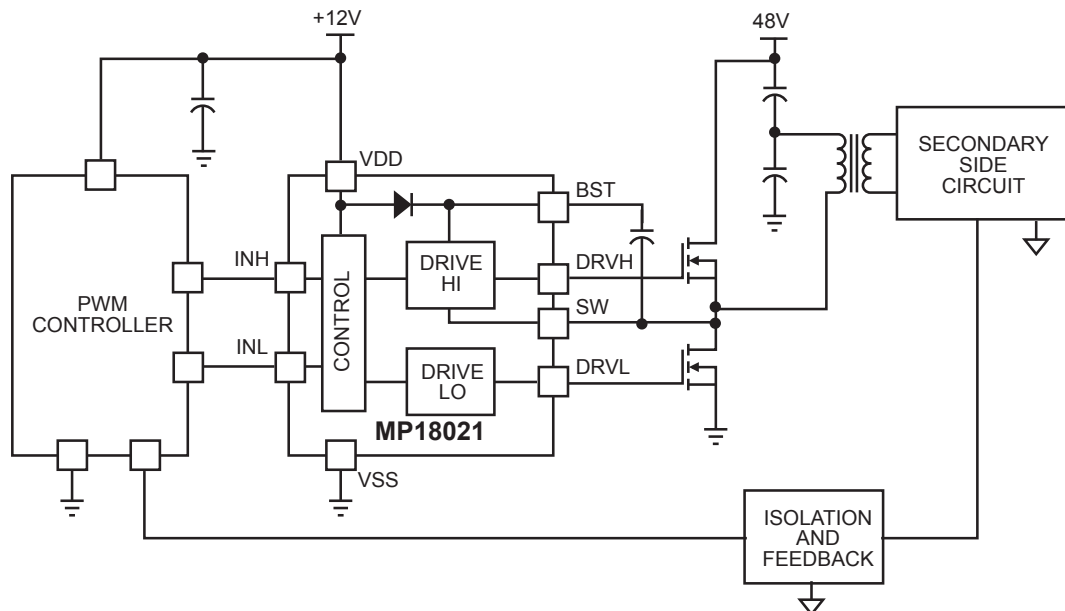
### APPLICATIONS

- Telecom half bridge power supplies
- Avionics DC-DC converters
- Two-switch forward converters
- Active clamp forward converters

All MPS parts are lead-free, halogen free, and adhere to the RoHS directive. For MPS green status, please visit MPS website under Quality Assurance.

"MPS" and "The Future of Analog IC Technology" are Registered Trademarks of Monolithic Power Systems, Inc.

### TYPICAL APPLICATION

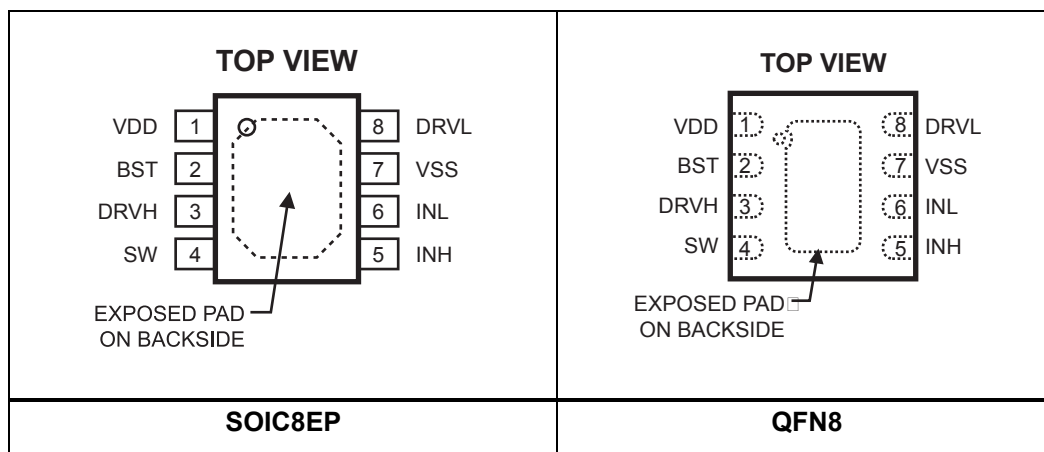


### ORDERING INFORMATION

Part Number*	Package	Top Marking	Free Air Temperature (T <sub>A</sub> )
MP18021HN	SOIC8EP	MP18021HN	-40°C to + 125°C
MP18021HQ	QFN8 (3x 3mm)	ABN	-40°C to + 125°C

\* For Tape & Reel, add suffix -Z (e.g. MP18021HN-Z);  
 For RoHS compliant packaging, add suffix -LF; (e.g. MP18021HN-LF-Z)  
 For Tape & Reel, add suffix -Z (e.g. MP18021HQ-Z);  
 For RoHS compliant packaging, add suffix -LF; (e.g. MP18021HQ-LF-Z)

### PACKAGE REFERENCE



### ABSOLUTE MAXIMUM RATINGS <sup>(1)</sup>

Supply Voltage (V <sub>DD</sub> )	-0.3V to +18V
SW Voltage (V <sub>SW</sub> )	-5.0V to 100V
BST Voltage (V <sub>BST</sub> )	-0.3V to 100V
BST to SW	-0.3V to +18V
DRVH to SW	-0.3V to +18V
All Other Pins	-0.3V to (V <sub>DD</sub> +0.3V)
Continuous Power Dissipation (T <sub>A</sub> = +25°C) <sup>(2)</sup>	
SOIC8 (Exposed Pad)	2.6W
QFN8 (3x3)	2.5W
Junction Temperature	150°C
Lead Temperature	260°C
Storage Temperature	-65°C to +150°C

### Recommended Operating Conditions <sup>(3)</sup>

Supply Voltage V <sub>DD</sub>	+9.0V to 16.0V
SW Voltage (V <sub>SW</sub> )	-1.0V to 100V-V <sub>DD</sub>
SW slew rate	<50V/nsec
Operating Junct. Temp (T <sub>J</sub> )	-40°C to +125°C

### Thermal Resistance <sup>(4)</sup>

	$\theta_{JA}$	$\theta_{JC}$
SOIC8 (Exposed Pad)	48	10
QFN8 (3x3)	50	12

#### Notes:

- Exceeding these ratings may damage the device.
- The maximum allowable power dissipation is a function of the maximum junction temperature T<sub>J</sub>(MAX), the junction-to-ambient thermal resistance  $\theta_{JA}$ , and the ambient temperature T<sub>A</sub>. The maximum allowable continuous power dissipation at any ambient temperature is calculated by P<sub>D</sub>(MAX)=(T<sub>J</sub>(MAX)-T<sub>A</sub>)/ $\theta_{JA}$ . Exceeding the maximum allowable power dissipation will cause excessive die temperature, and the regulator will go into thermal shutdown. Internal thermal shutdown circuitry protects the device from permanent damage.
- The device is not guaranteed to function outside of its operating conditions.
- Measured on JESD51-7, 4-layer PCB.

## ELECTRICAL CHARACTERISTICS

$V_{DD} = V_{BST} - V_{SW} = 12V$ ,  $V_{SS} = V_{SW} = 0V$ , No load at DRVH and DRVL,  $T_A = +25^\circ C$ , unless otherwise noted.

Parameter	Symbol	Condition	Min	Typ	Max	Units
<b>Supply Currents</b>						
VDD quiescent current	$I_{DDQ}$	INL=INH=0		100	150	$\mu A$
VDD operating current	$I_{DDO}$	fsw=500kHz		2.8	3.5	mA
Floating driver quiescent current	$I_{BSTQ}$	INL=INH=0		60	90	$\mu A$
Floating driver operating current	$I_{BSTO}$	fsw=500kHz		2.1	3	mA
Leakage Current	$I_{LK}$	BST=SW=100V		0.05	1	$\mu A$
<b>Inputs</b>						
INL/INH High				2	2.4	V
INL/INH Low			1	1.4		V
INL/INH internal pull-down resistance	$R_{IN}$			185		k $\Omega$
<b>Under Voltage Protection</b>						
VDD rising threshold	$V_{DDR}$		7.7	8.1	8.5	V
VDD hysteresis	$V_{DDH}$			0.5		V
(BST-SW) rising threshold	$V_{BSTR}$		6.7	7.1	7.5	V
(BST-SW) hysteresis	$V_{BSTH}$			0.55		V
<b>Bootstrap Diode</b>						
Bootstrap diode VF @ 100uA	$V_{F1}$			0.5		V
Bootstrap diode VF @ 100mA	$V_{F2}$			0.9		V
Bootstrap diode dynamic R	$R_D$	@ 100mA		2.5		$\Omega$
<b>Low Side Gate Driver</b>						
Low level output voltage	$V_{OLL}$	$I_O = 100mA$		0.15	0.22	V
High level output voltage to rail	$V_{OHL}$	$I_O = -100mA$		0.45	0.6	V
Peak pull-up current	$I_{OHL}$	$V_{DRVL} = 0V, V_{DD} = 12V$		1.5		A
		$V_{DRVL} = 0V, V_{DD} = 16V$		2.5		A
Peak pull-down current	$I_{OLL}$	$V_{DRVL} = V_{DD} = 12V$		2.5		A
		$V_{DRVL} = V_{DD} = 16V$		3.5		A
<b>Floating Gate Driver</b>						
Low level output voltage	$V_{OLH}$	$I_O = 100mA$		0.15	0.22	V
High level output voltage to rail	$V_{OHH}$	$I_O = -100mA$		0.45	0.6	V
Peak pull-up current	$I_{OHH}$	$V_{DRVH} = 0V, V_{DD} = 12V$		1.5		A
		$V_{DRVH} = 0V, V_{DD} = 16V$		2.5		A
Peak pull-down current	$I_{OLH}$	$V_{DRVH} = V_{DD} = 12V$		2.5		A
		$V_{DRVH} = V_{DD} = 16V$		3.5		A

**ELECTRICAL CHARACTERISTICS (continued)**

$V_{DD} = V_{BST} - V_{SW} = 12V$ ,  $V_{SS} = V_{SW} = 0V$ , No load at DRVH and DRVL,  $T_A = +25^\circ C$ , unless otherwise noted.

Parameter	Symbol	Condition	Min	Typ	Max	Units
<b>Switching Spec. --- Low Side Gate Driver</b>						
Turn-off propagation delay INL falling to DRVL falling	$T_{DLFF}$			16		ns
Turn-on propagation delay INL rising to DRVL rising	$T_{DLRR}$			16		
DRVL rise time		$C_L = 1nF$		12		ns
DRVL fall time		$C_L = 1nF$		9		ns
<b>Switching Spec. --- Floating Gate Driver</b>						
Turn-off propagation delay INL falling to DRVH falling	$T_{DHFF}$			16		ns
Turn-on propagation delay INL rising to DRVH rising	$T_{DHRR}$			16		ns
DRVH rise time		$C_L = 1nF$		12		ns
DRVH fall time		$C_L = 1nF$		9		ns
<b>Switching Spec. --- Matching</b>						
Floating driver turn-off to low side drive turn-on	$T_{MON}$			1	5	ns
Low side driver turn-off to floating driver turn-on	$T_{MOFF}$			1	5	ns
Minimum input pulse width that changes the output	$T_{PW}$				50 <sup>(5)</sup>	ns
Bootstrap diode turn-on or turn- off time	$T_{BS}$			10 <sup>(5)</sup>		ns
<b>Over Temperature Protection<sup>(5)</sup></b>						
OTP entry threshold				160		°C
OTP recovery threshold				140		
OTP hysteresis				20		

**Note:**

5) Derived from bench characterization. Not tested in production.

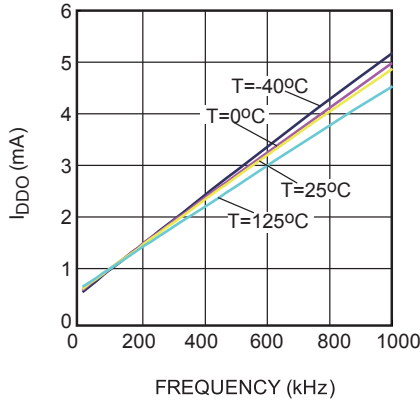
## PIN FUNCTIONS

Pin #	Name	Description
1	VDD	Supply input. This pin supplies power to all the internal circuitry. A decoupling capacitor to ground must be placed close to this pin to ensure stable and clean supply.
2	BST	Bootstrap. This is the positive power supply for the internal floating high-side MOSFET driver. Connect a bypass capacitor between this pin and SW pin.
3	DRVH	Floating driver output.
4	SW	Switching node.
5	INH	Control signal input for the floating driver.
6	INL	Control signal input for the low side driver.
7	VSS, Exposed Pad	Chip ground. Connect to Exposed pad to VSS for proper thermal operation.
8	DRVL	Low side driver output.

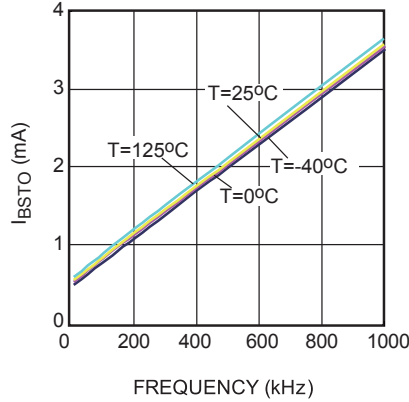
## TYPICAL PERFORMANCE CHARACTERISTICS

$V_{DD}=12V$ ,  $V_{SS}=V_{SW}=0V$ ,  $T_A=+25^\circ C$ , unless otherwise noted.

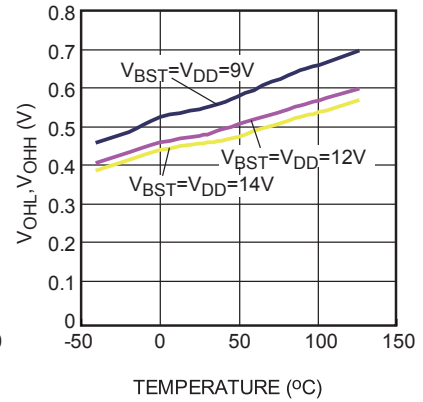
**$I_{DDO}$  Operation Current vs. Frequency**



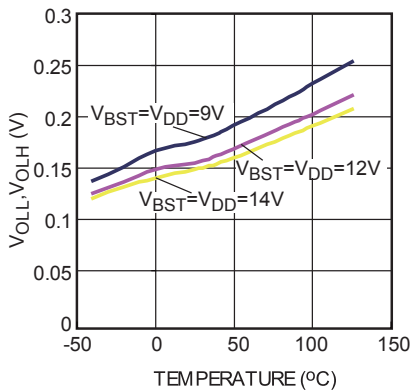
**$I_{BSTO}$  Operation Current vs. Frequency**



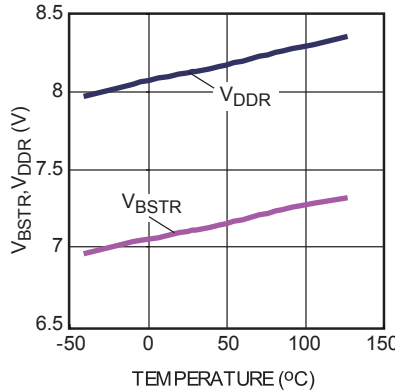
**High Level Output Voltage vs. Temperature**



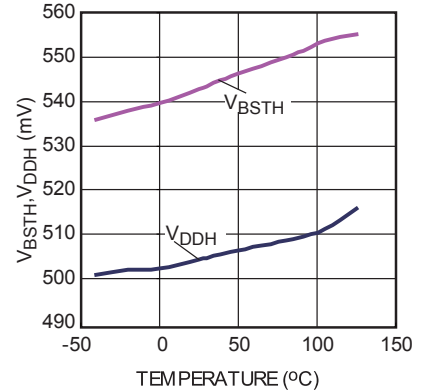
**Low Level Output Voltage vs. Temperature**



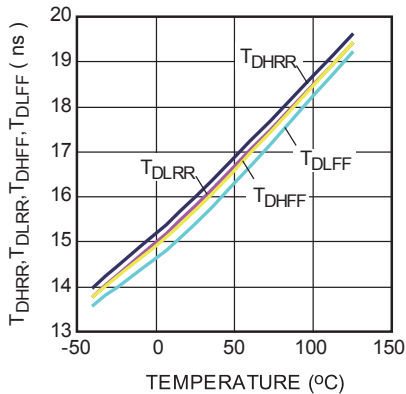
**Undervoltage Lockout Threshold vs. Temperature**



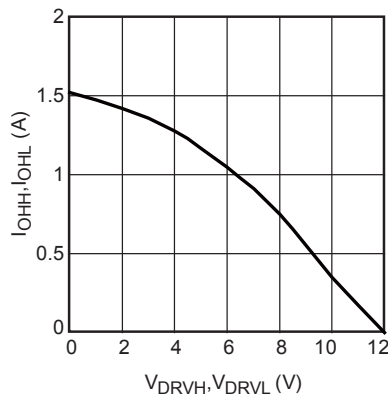
**Undervoltage Lockout Hysteresis vs. Temperature**



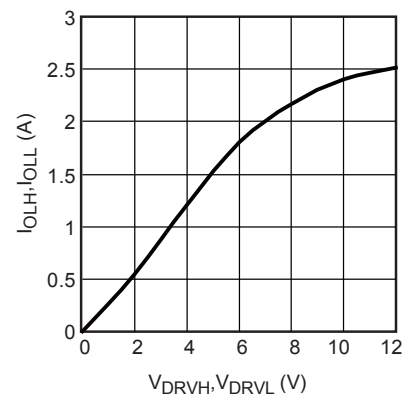
**Propagation Delay vs. Temperature**



**Peak Pull-up Current vs. Output Voltage**



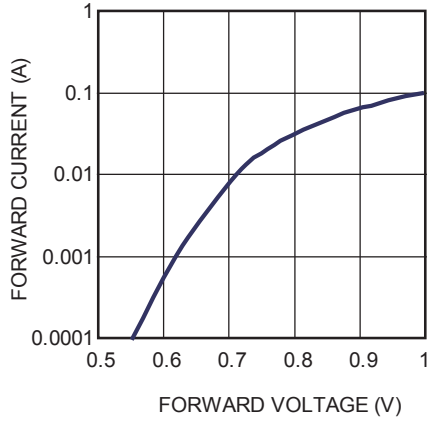
**Peak Pull-down Current vs. Output Voltage**



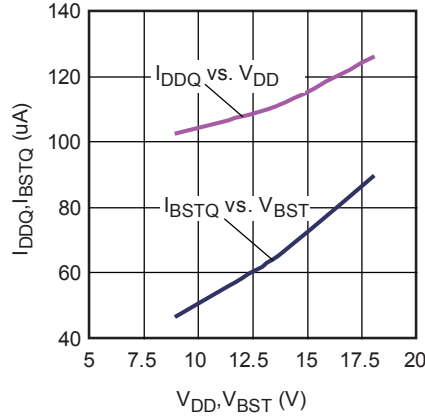
**TYPICAL PERFORMANCE CHARACTERISTICS (continued)**

$V_{DD} = 12V$ ,  $V_{SS} = V_{SW} = 0V$ ,  $T_A = +25^\circ C$ , unless otherwise noted.

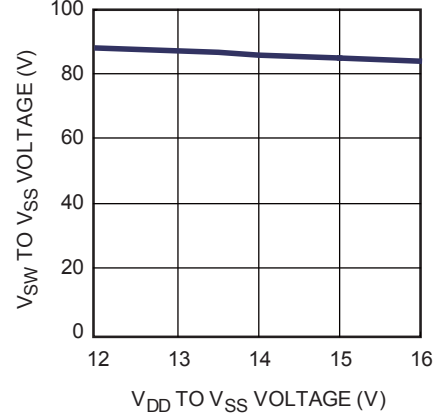
**Bootstrap Diode I-V Characteristics**



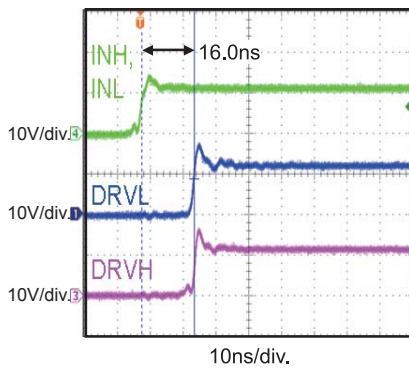
**Quiescent Current vs. Voltage**



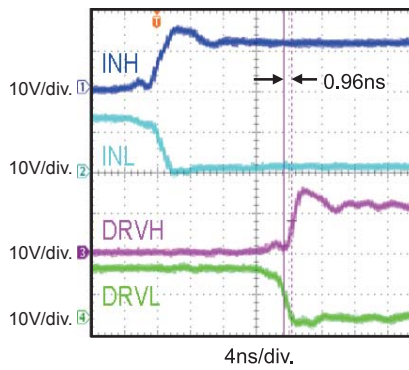
**Maximum VSW Voltage vs. VDD Voltage**



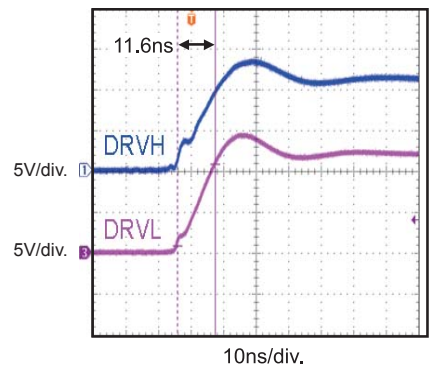
**Turn-on Propagation Delay**



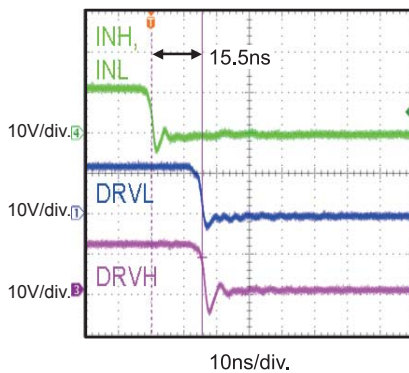
**Gate Drive Matching TMOFF**



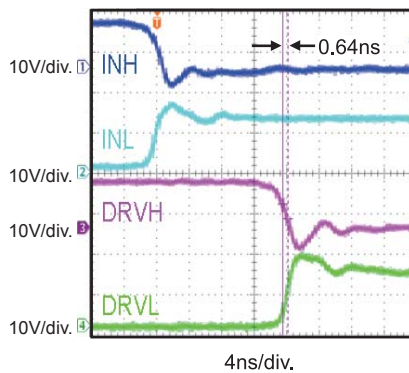
**Drive Rise Time (1nF Load)**



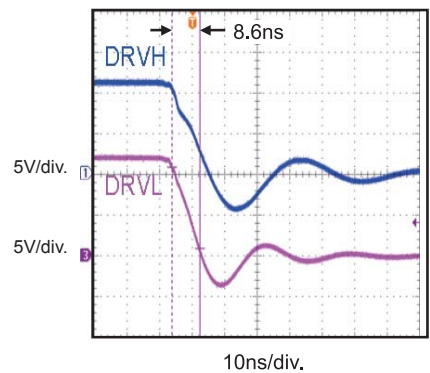
**Turn-off Propagation Delay**



**Gate Drive Matching TMON**



**Drive Fall Time (1nF Load)**



BLOCK DIAGRAM

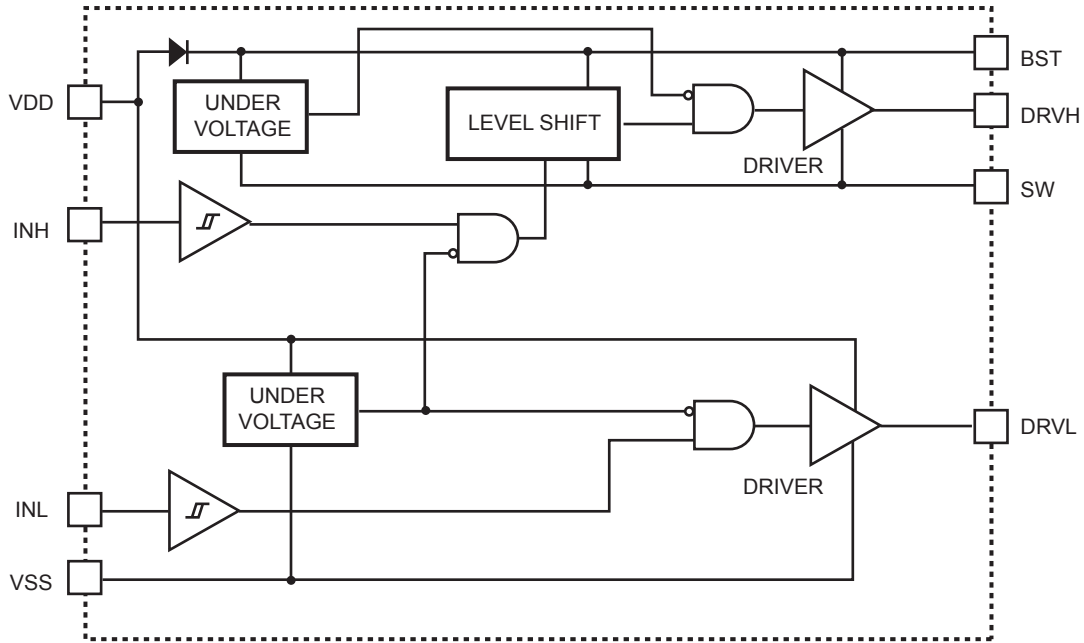


Figure 1—Function Block Diagram

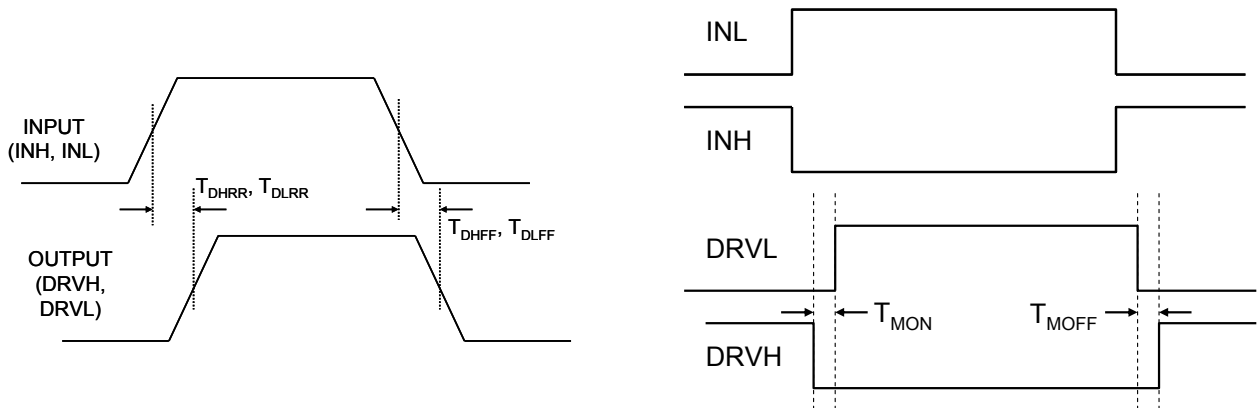
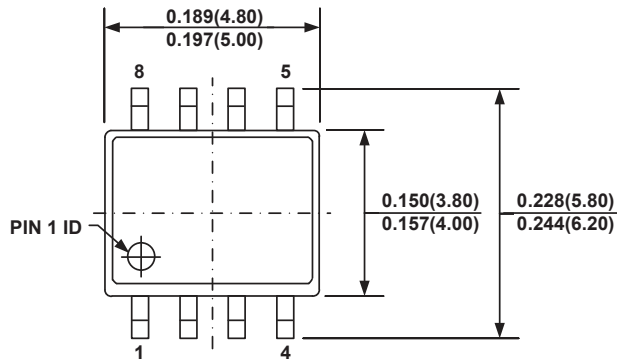
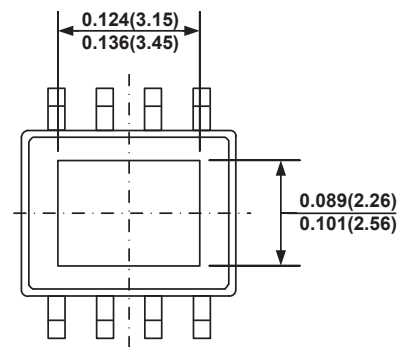
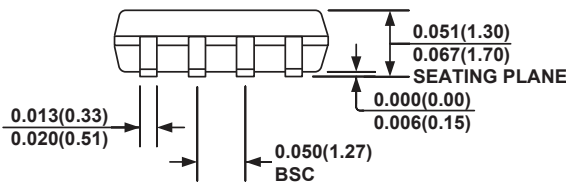
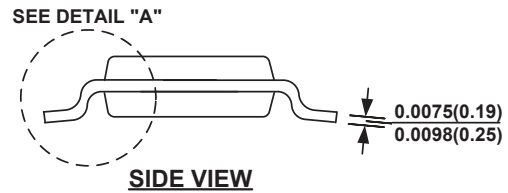
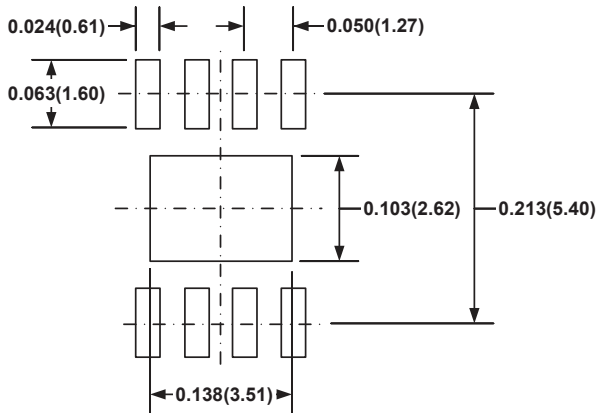
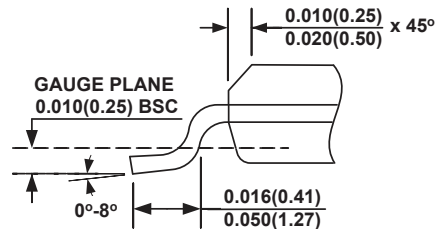
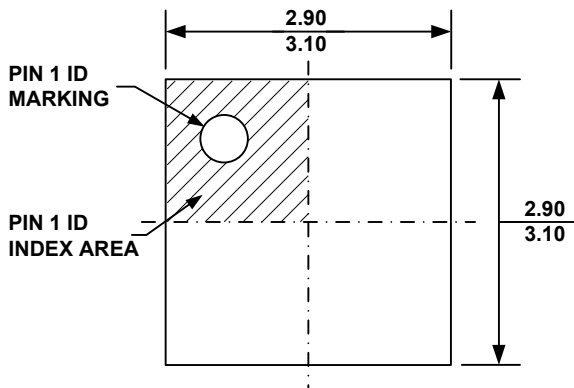
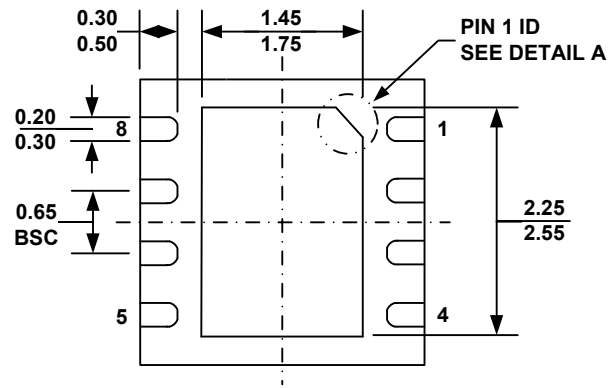
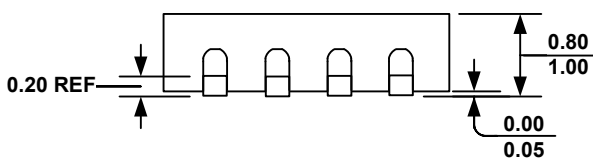
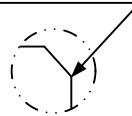
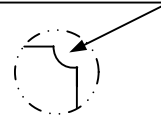
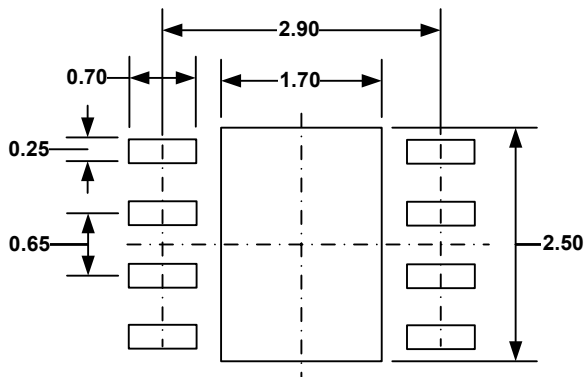


Figure 2—Timing Diagram



**PACKAGE INFORMATION**
**SOIC8 (EXPOSED PAD)**

**TOP VIEW**

**BOTTOM VIEW**

**FRONT VIEW**

**SIDE VIEW**

**RECOMMENDED LAND PATTERN**

**DETAIL "A"**
**NOTE:**

- 1) CONTROL DIMENSION IS IN INCHES. DIMENSION IN BRACKET IS IN MILLIMETERS.
- 2) PACKAGE LENGTH DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
- 3) PACKAGE WIDTH DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSIONS.
- 4) LEAD COPLANARITY (BOTTOM OF LEADS AFTER FORMING) SHALL BE 0.004" INCHES MAX.
- 5) DRAWING CONFORMS TO JEDEC MS-012, VARIATION BA.
- 6) DRAWING IS NOT TO SCALE.

**QFN8 (3mm×3mm)**

**TOP VIEW**

**BOTTOM VIEW**

**SIDE VIEW**
**PIN 1 ID OPTION A  
0.30x45° TYP.**

**PIN 1 ID OPTION B  
R0.20 TYP.**

**DETAIL A**

**RECOMMENDED LAND PATTERN**
**NOTE:**

- 1) ALL DIMENSIONS ARE IN MILLIMETERS.
- 2) EXPOSED PADDLE SIZE DOES NOT INCLUDE MOLD FLASH.
- 3) LEAD COPLANARITY SHALL BE 0.10 MILLIMETER MAX.
- 4) DRAWING CONFORMS TO JEDEC MO-229, VARIATION VEEC-2.
- 5) DRAWING IS NOT TO SCALE.

**NOTICE:** The information in this document is subject to change without notice. Users should warrant and guarantee that third party Intellectual Property rights are not infringed upon when integrating MPS products into any application. MPS will not assume any legal responsibility for any said applications.



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



#### Как с нами связаться

**Телефон:** 8 (812) 309 58 32 (многоканальный)

**Факс:** 8 (812) 320-02-42

**Электронная почта:** [org@eplast1.ru](mailto:org@eplast1.ru)

**Адрес:** 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.